



## BTX18-100/BTX18-200/BTX18-300 BTX18-400/BTX18-500

### SILICON THYRISTORS

The BTX18 series is a range of p-gate reverse blocking thyristors, in a TO-39 metal enveloppe, intended for use in general low power applications up to a A average on-state current.

### RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

#### Anode to Cathode - Ratings

Voltage<sup>1)</sup>

Symbol	Ratings	BTX18-100	BTX18-200	BTX18-300	BTX18-400	BTX18-500	
$V_R$	Continuous Reverse Voltage	100	200	300	400	500	V
$V_{RWM}$	Crest Working Reverse Voltage	100	200	300	400	500	V
$V_{RRM}$	Repetitive Peak Reverse Voltage ( $\delta = 0.01$ ; f=50Hz)	120	240	350	500	600	V
$V_{RSM}$	Non-repetitive peak reverse voltage ( $t < 10ms$ )	120	240	350	500	600	V
$V_{DWM}$	Crest Working off-state Voltage	100	200	300	400	500	V
$V_D$	Continuous off-state Voltage	100	200	300	400	500	V
$V_{DRM}$	Repetitive peak off-state voltage ( $\delta = 0.01$ ; f=50Hz)	120	240	350	500	600	V <sup>2)</sup>
$V_{DSM}$	Non-repetitive peak off-state voltage ( $t < 10ms$ )	120	240	350	500	600	V <sup>2)</sup>

#### Currents

Symbol	Ratings	BTX18-100	BTX18-200	BTX18-300	BTX18-400	BTX18-500	
$I_{T(AV)}$	Average on-state current (averaged over any 20 ms period)	$T_{CASE}=105^\circ C$ $T_{AMB}=60^\circ C$ , in free air		Max : 1.0			A
$I_T$	On-state Current (D.C.) $T_{CASE}=100^\circ C$			Max : 250			mA
$I_{T(RMS)}$	RMS on-state Current			Max : 1.6			A

# BTX18-100/BTX18-200/BTX18-300

## BTX18-400/BTX18-500

Symbol	Ratings	BTX18-100	BTX18-200	BTX18-300	BTX18-400	BTX18-500
$I_{TRM}$	Repetitive Peak on-state Current			Max : 10		A
$I_{TSM}$	Non-repetitive peak on-state current $t=10\text{ms}$ ; $T_J=125^\circ\text{C}$ prior to surge			10 A		V
$T_J$ $T_{stg}$	Junction Temperature Storage Temperature			Max : $125^\circ\text{C}$ -55 to $+125^\circ\text{C}$		$^\circ\text{C}$

- These ratings apply for zero or negative bias on the gate with respect to the cathode, and when a resistor  $R<1\text{ k}\Omega$  is connected between gate and cathode
- The device is not suitable for operation in the forward breakdown mode.

### Gate to Cathode - Ratings

With  $1\Omega$  resistor between gate and cathode

Symbol	Ratings	BTX18-100	BTX18-200	BTX18-300	BTX18-400	BTX18-500
$V_{FGM}$	Forward Peak Voltage			Max : 10 V		V
$V_{RGM}$	Reverse Peak Voltage			Max : 5 V		V
$I_{FGM}$	Forward Peak Current			Max : 0.2		A
$P_{G(AV)}$	Average Power Dissipation (averaged over any 20 ms period)			Max : 0.05		W
$P_{GM}$	Peak Power Dissipation			Max : 0.5		W

### Temperatures

Symbol	Ratings	BTX18-100	BTX18-200	BTX18-300	BTX18-400	BTX18-500
$R_{th j-c}$	From Junction to Case			10		$^\circ\text{C/W}$
$R_{th j-a}$	From Junction to Ambient			200		$^\circ\text{C/W}$
$Z_{th j-c}$	Transient Thermal Resistance ( $t=10\text{ ms}$ )			2.5		$^\circ\text{C/W}$

### Anode to Cathode - Characteristics

Symbol	Ratings	BTX18-100	BTX18-200	BTX18-300	BTX18-400	BTX18-500	
$V_T$	On State Voltage $I_T=1.0\text{ A}, T_J=25^\circ\text{C}$	<	1.5	1.5	1.5	1.5	$\text{V}^1)$

# BTX18-100/BTX18-200/BTX18-300

## BTX18-400/BTX18-500

Symbol	Ratings		BTX18 -100	BTX18 -200	BTX18 -300	BTX18 -400	BTX18 -500	
$I_{RM}$	Peak Reverse Current $V_{RM}=V_{RWmax}$ ; $T_j=125^\circ C$	<	800	400	275	200	160	$\mu A$
$I_{DM}$	Peak off-state Current $V_{DM}=V_{DWmax}$ ; $T_j=125^\circ C$	<	800	400	275	200	160	$\mu A$
$I_L$	Latching current, $T_j=125^\circ C$				Typ : 10			$mA$
$I_H$	Holding Current ; $T_j=25^\circ C$	<			5.0 <sup>2)</sup>			$mA$

### Gate to Cathode – Characteristics

Symbol	Ratings		BTX18 -100	BTX18 -200	BTX18 -300	BTX18 -400	BTX18 -500	
$V_{GT}$	Voltage that will trigger all devices $T_j=25^\circ C$	>			2.0			$V$
$V_{GD}$	Voltage that will not trigger any device $T_j=125^\circ C$	<			200			$mV$
$I_{GT}$	Current that will trigger all devices $T_j=25^\circ C$	>			5.0			$mA$

### Switching Characteristics

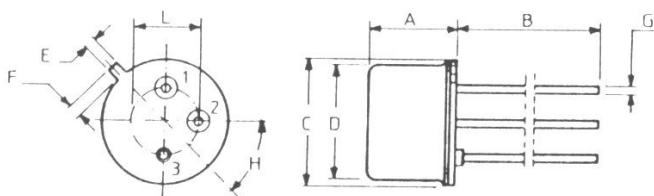
Symbol	Ratings		BTX18 -100	BTX18 -200	BTX18 -300	BTX18 -400	BTX18 -500	
Turn off time when switched from $IT=300\text{ mA}$ to $IR=175\text{ mA}$	$T_j=25^\circ C$ $T_j=125^\circ C$	$t_q$			Type : 20			$\mu s$
$I_{DM}$	Peak off-state Current $V_{DM}=V_{DWmax}$ ; $T_j=125^\circ C$	<	800	400	275	200	160	$\mu s$

- 1)  $V_T$  is measured along the leads at 1 cm from the case
- 2) Measured under the following conditions :
  - Anode supply voltage = +6.0V
  - Initial on-state current after gate triggering = 50mA
  - The current is reduced until the device turns off.

# **BTX18-100/BTX18-200/BTX18-300 BTX18-400/BTX18-500**

## **MECHANICAL DATA CASE TO-39**

DIMENSIONS		
	mm	inches
A	6,71	0,26
B	13,2	0,51
C	9,23	0,36
D	8,34	0,32
E	0,8	0,03
F	0,8	0,03
G	0,42	0,016
H	45°	
L	4,97	0,2



Pin 1 :	Kathode
Pin 2 :	Gate
Pin 3 :	Anode

This datasheet has been downloaded from:

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Datasheets for electronic components.